

High Efficiency Amplifiers

Aethercomm manufactures high efficiency amplifier modules utilizing the latest in Gallium Nitride (GaN) technology to achieve 50% to 70% power added efficiency (PAE). With lower parasitic capacitance and higher breakdown voltage, commercial GaN devices are ideal for higher efficient amplifier modes. Aethercomm's success in producing such amplifiers, employing commercial devices, leads the way into future military and commercial system designs. These high efficiency amplifiers are custom in nature and highly proprietary; therefore, limited standard products are displayed. Below are bands with typical power levels and efficiencies with the different classes of amplifiers.

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For other frequencies, power levels and more high efficiency amplifiers, please contact the factory with your specific requirements.

| Frequency | Output Power | Efficiencies Available Class D, E, F, J & S |
|-----------|--------------|------------------------------------------------|
| UHF | 200+ watts | 50-75% depending on bandwidth |
| L Band | 200+ watts | 50-75% depending on bandwidth |
| S Band | 100+ watts | 50-75% depending on bandwidth |

SSPA 0.020-0.520-125



- Operation from 20 MHz to 520 MHz min
- Small Signal Gain 58 dB typ
- 50+% typ Power Added Efficiency
- 125 Watts P3dB typ
- Gallium nitride broadband power amplifier

SSPA 0.020-1.000-100



- Operation from 20 MHz to 1000 MHz min
- Small Signal Gain 58 dB typ
- 40 to 60% typ Power Added Efficiency
- 100 Watts P3dB typ
- Gallium nitride broadband power amplifier